

Central™ Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMOSH-3 type is a Silicon Schottky diode, epoxy molded in an ULTRAmi™ surface mount package, designed for fast switching applications requiring a low forward voltage drop. Marking code is 53.

MAXIMUM RATINGS: (T_A=25°C)

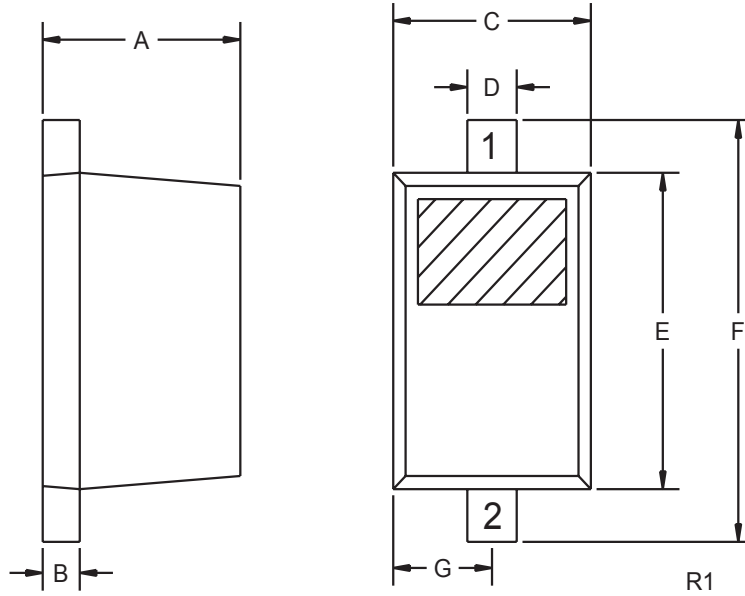
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	30	V
Continuous Forward Current	I _F	100	mA
Peak Repetitive Forward Current	I _{FRM}	350	mA
Forward Surge Current, tp=10ms	I _{FSM}	750	mA
Power Dissipation	P _D	250	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
B _V R	I _R =100μA	30			V
V _F	I _F =2.0mA		0.29	0.33	V
V _F	I _F =15mA		0.40	0.45	V
V _F	I _F =100mA		0.74	1.00	V
I _R	V _R =25V		90	500	nA
I _R	V _R =25V, T _A =100°C		25	100	μA
C _T	V _R =1.0V, f=1 MHz		7.0		pF
t _{rr}	I _F =I _R =10mA, I _{rr} =1.0mA, R _L =100Ω			5.0	ns

R1 (20-July 2001)

SOD-523 - MECHANICAL OUTLINE



Lead Code:

- 1) Cathode
- 2) Anode

MARKING CODE: 53

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.004	0.008	0.10	0.20
C	0.028	0.035	0.70	0.90
D	0.008	0.011	0.20	0.28
E	0.039	0.055	1.00	1.40
F	0.055	0.071	1.40	1.80
G	0.016		0.40	

SOD-523 (REV: R1)

R1 (20-July 2001)